



STB9NK90Z, STF9NK90Z STP9NK90Z, STW9NK90Z

N-channel 900 V, 1.1 Ω , 8 A, TO-220, TO-220FP, D²PAK, TO-247
Zener-protected SuperMESH™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max.	I _D	P _w
STB9NK90Z	900V	<1.3 Ω	8A	160 W
STW9NK90Z				160 W
STP9NK90Z				160 W
STF9NK90Z				40 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized

Application

- Switching applications

Description

The SuperMESH™ series is obtained through an optimization of STMicroelectronics' well-established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly lower, it also ensures very good dv/dt capability for the most demanding applications. This series complement STs' full range of high voltage power MOSFETs.

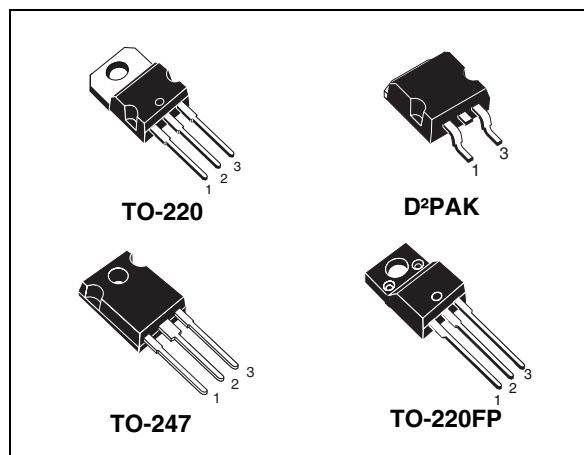


Figure 1. Internal schematic diagram

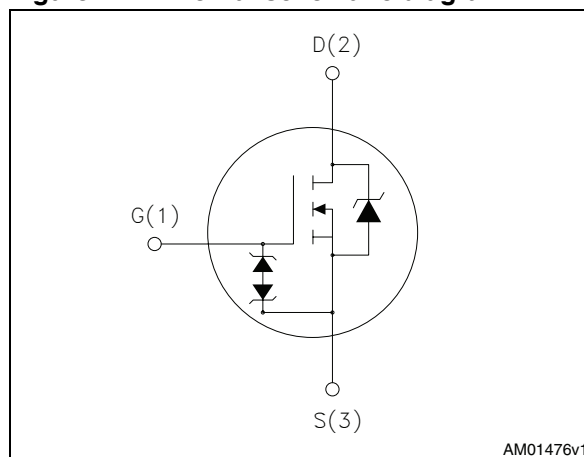


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB9NK90Z	B9NK90	D ² PAK	Tape and reel
STF9NK90Z	F9NK90Z	TO-220FP	Tube
STP9NK90Z	P9NK90Z	TO-220	
STW9NK90Z	W9NK90Z	TO-247	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, D ² PAK TO-247	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	900		V
V_{GS}	Gate-source voltage	± 30		V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	8	8 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	5	5 ⁽¹⁾	A
$I_{DM}^{(2)}$	Drain current (pulsed)	32	32 ⁽¹⁾	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	160	40	W
	Derating Factor	1.28	0.32	W/ $^{\circ}\text{C}$
Vesd(G-S)	G-S ESD (HBM C=100 pF, R=1.5 k Ω)	4		KV
dv/dt ⁽³⁾	Peak diode recovery voltage slope	4.5		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{ s}; T_C=25\text{ }^{\circ}\text{C}$)	--	2500	V
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 150		$^{\circ}\text{C}$

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 10\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq T_{Jmax}$.

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		TO-220 D ² PAK	TO-220FP	TO-247	
$R_{thj-case}$	Thermal resistance junction-case max	0.78	3.1	0.78	$^{\circ}\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5		50	$^{\circ}\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300			$^{\circ}\text{C}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max.)	8	A
E_{AS}	Single pulse avalanche energy (starting $T_J=25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$) (see Figure 22)(see Figure 23)	300	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	900			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$, $V_{DS} = \text{max rating @ } 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 3.6\text{ A}$		1.1	1.3	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	2115	-	pF
C_{oss}	Output capacitance			190		pF
C_{rss}	Reverse transfer capacitance			40		pF
$C_{oss\text{ eq}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{ to }720\text{ V}$	-	115	-	pF
Q_g	Total gate charge	$V_{DD} = 720\text{ V}$, $I_D = 8\text{ A}$ $V_{GS} = 10\text{ V}$ Figure 20	-	72	-	nC
Q_{gs}	Gate-source charge			14		nC
Q_{gd}	Gate-drain charge			38		nC

1. $C_{oss\text{ eq}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 450\text{ V}$, $I_D = 4\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ Figure 19 Figure 24	-	22	-	ns
t_r	Rise Time			13		ns
$t_{d(off)}$	Turn-off delay time		-	55	-	ns
t_f	Fall time			28		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		8	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				32	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 8\text{ A}$, $V_{GS}=0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 8\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 50\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ Figure 21	-	950		ns
Q_{rr}	Reverse recovery charge			10		μC
I_{RRM}	Reverse recovery current			21		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 9. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ (open drain)	30	-		V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK

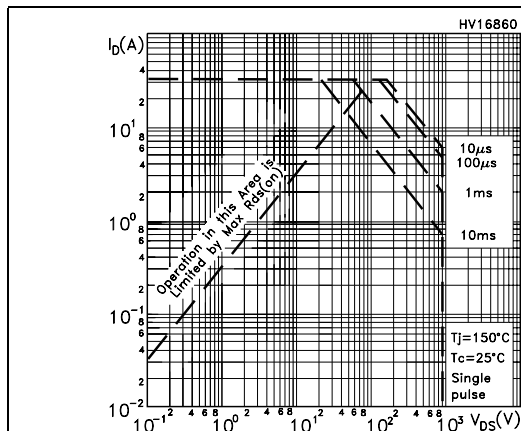


Figure 3. Thermal impedance for TO-220, D²PAK

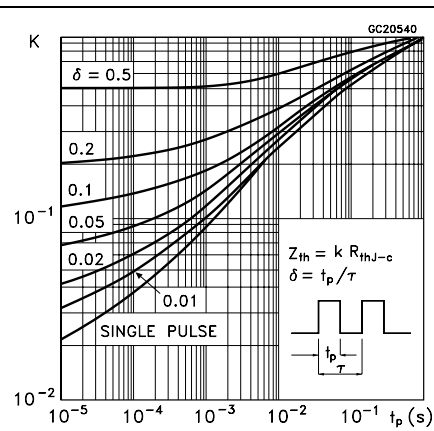


Figure 4. Safe operating area for TO-220FP

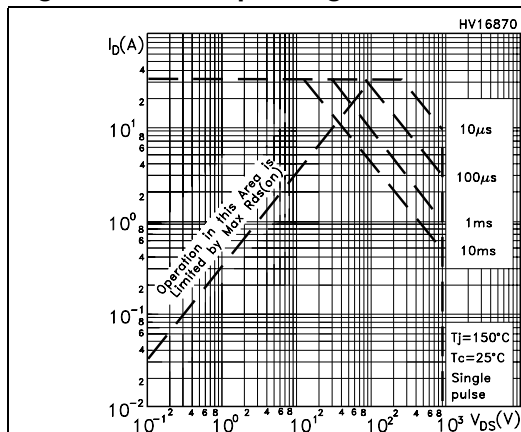


Figure 5. Thermal impedance for TO-220FP

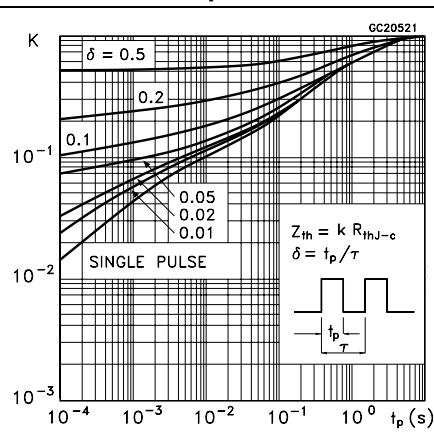


Figure 6. Safe operating area for TO-247

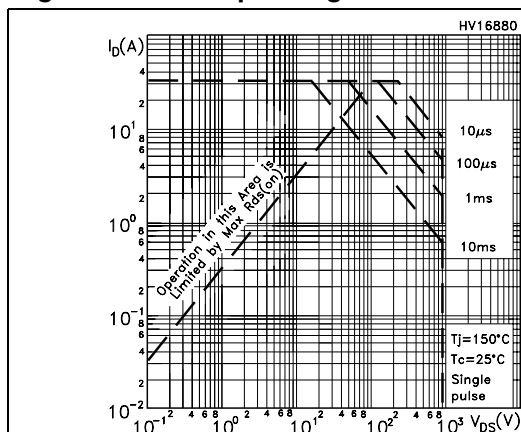


Figure 7. Thermal impedance for TO-247

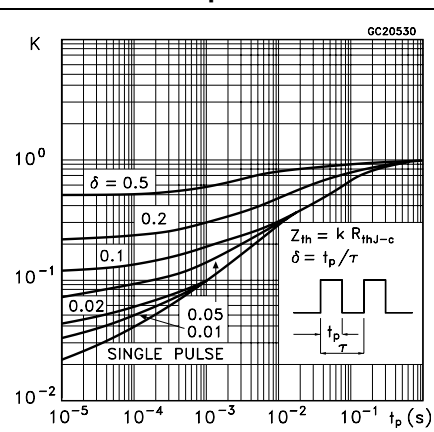


Figure 8. Output characteristics

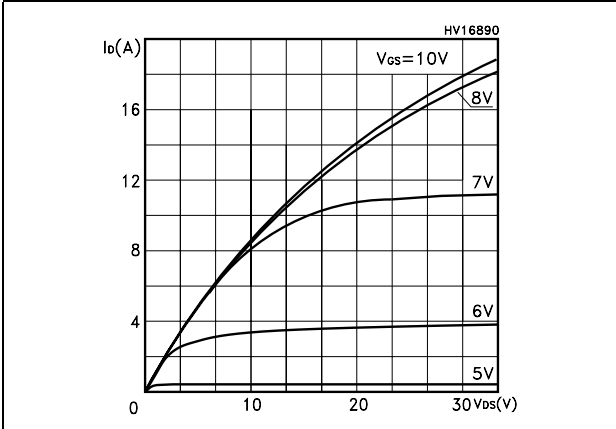


Figure 9. Transfer characteristics

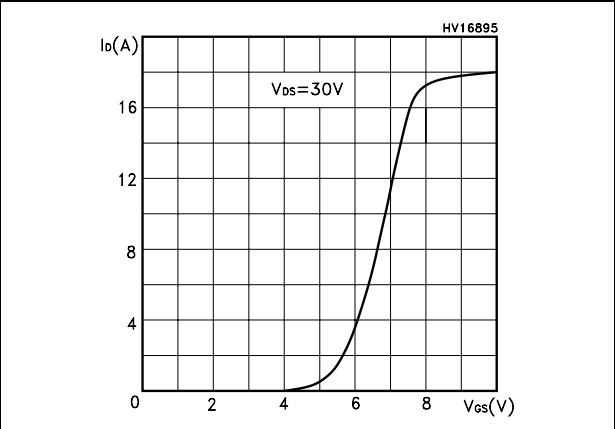


Figure 10. Transconductance

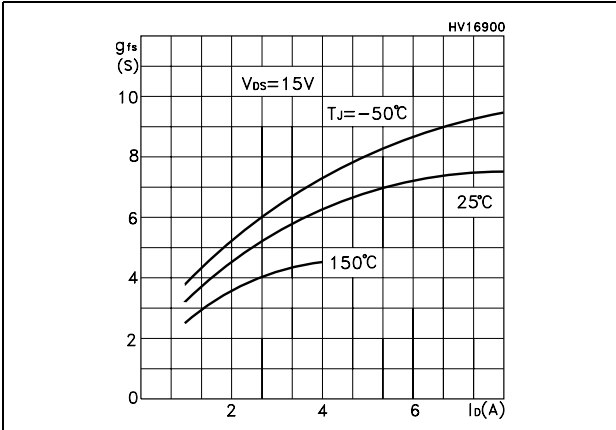


Figure 11. Static drain-source on resistance

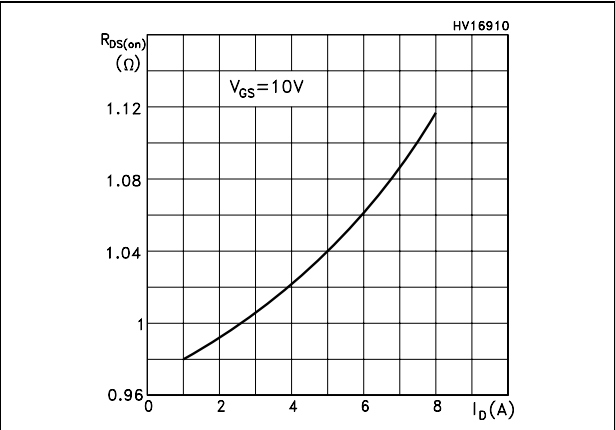


Figure 12. Gate charge vs gate-source voltage

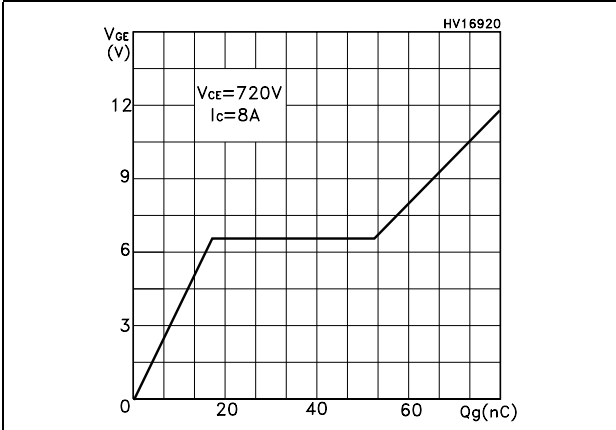


Figure 13. Capacitance variations

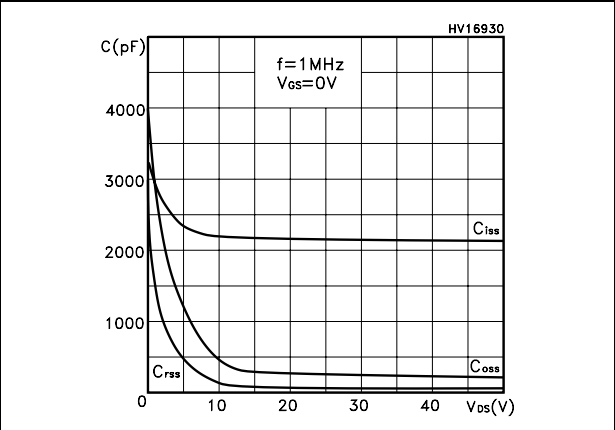


Figure 14. Normalized gate threshold voltage vs temperature

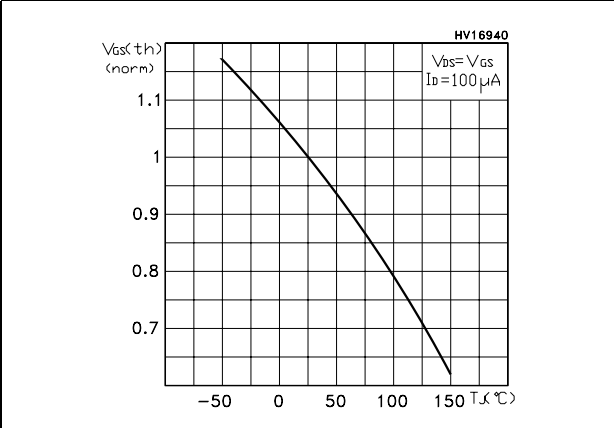


Figure 15. Normalized on resistance vs temperature

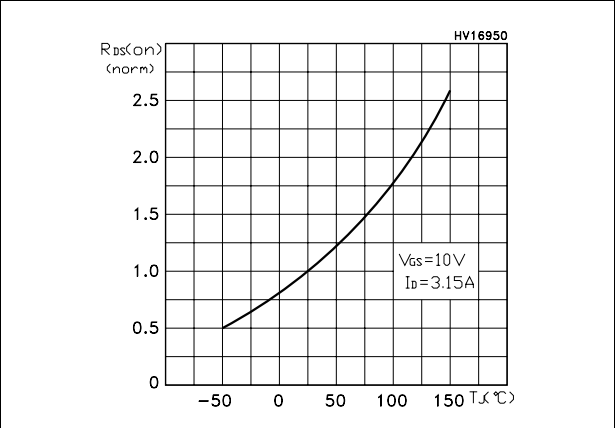


Figure 16. Source-drain diode forward characteristics

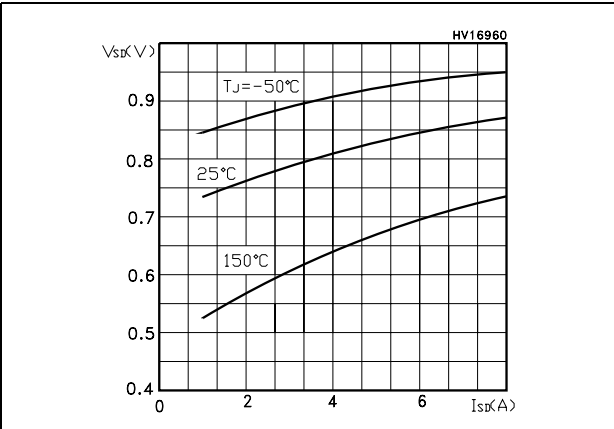


Figure 17. Normalized BVDS vs temperature

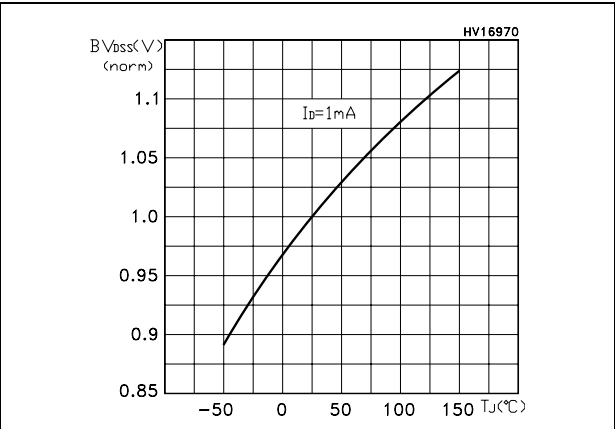
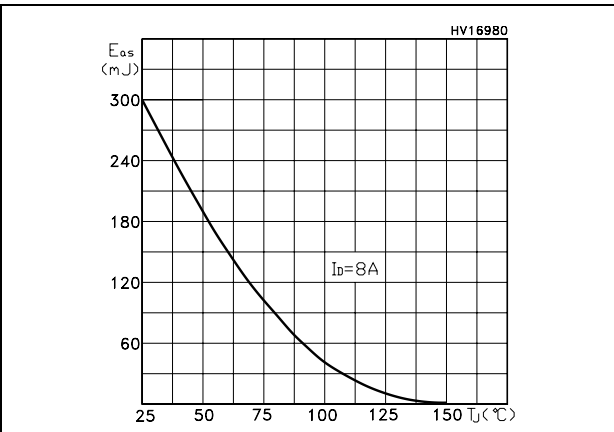


Figure 18. Maximum avalanche energy vs temperature



3 Test circuits

Figure 19. Switching times test circuit for resistive load

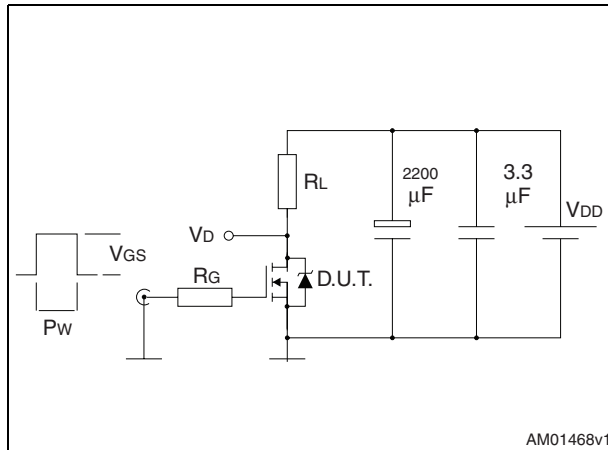


Figure 20. Gate charge test circuit

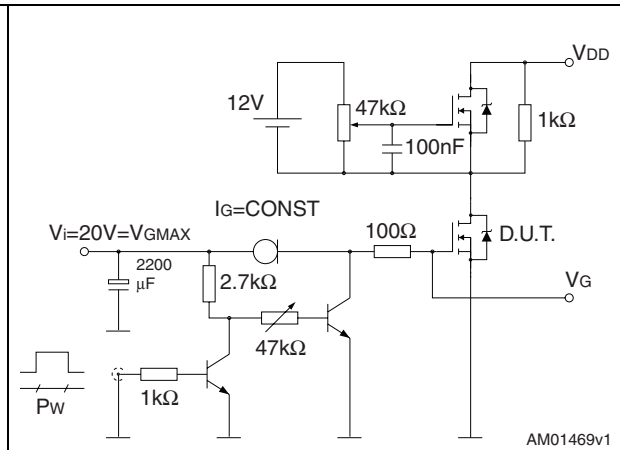


Figure 21. Test circuit for inductive load switching and diode recovery times

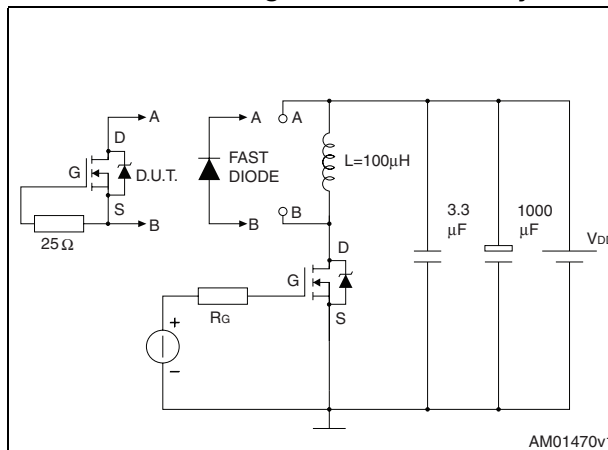


Figure 22. Unclamped Inductive load test circuit

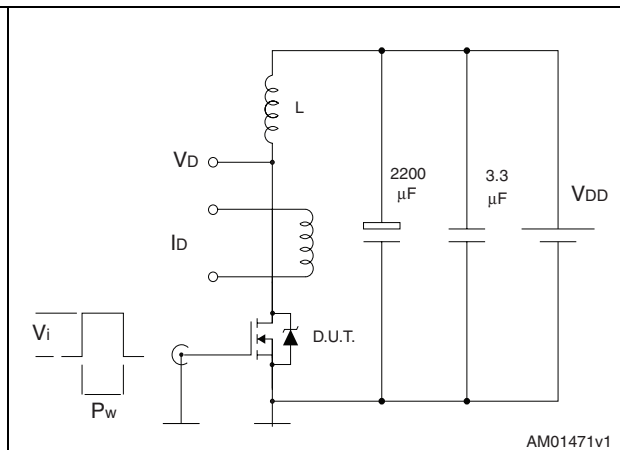


Figure 23. Unclamped inductive waveform

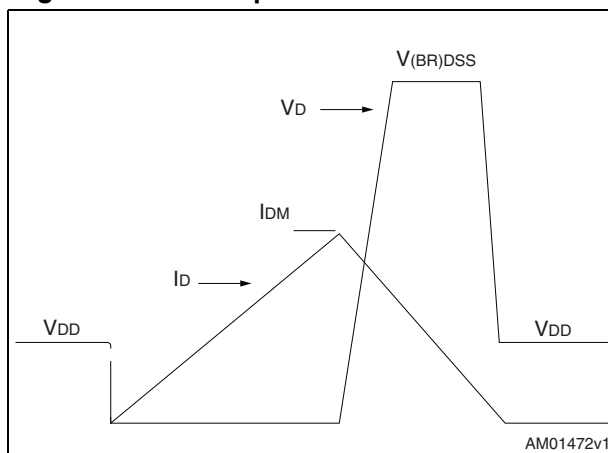
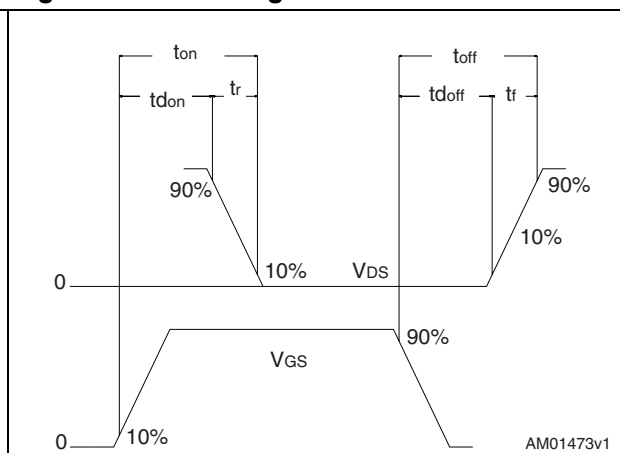


Figure 24. Switching time waveform



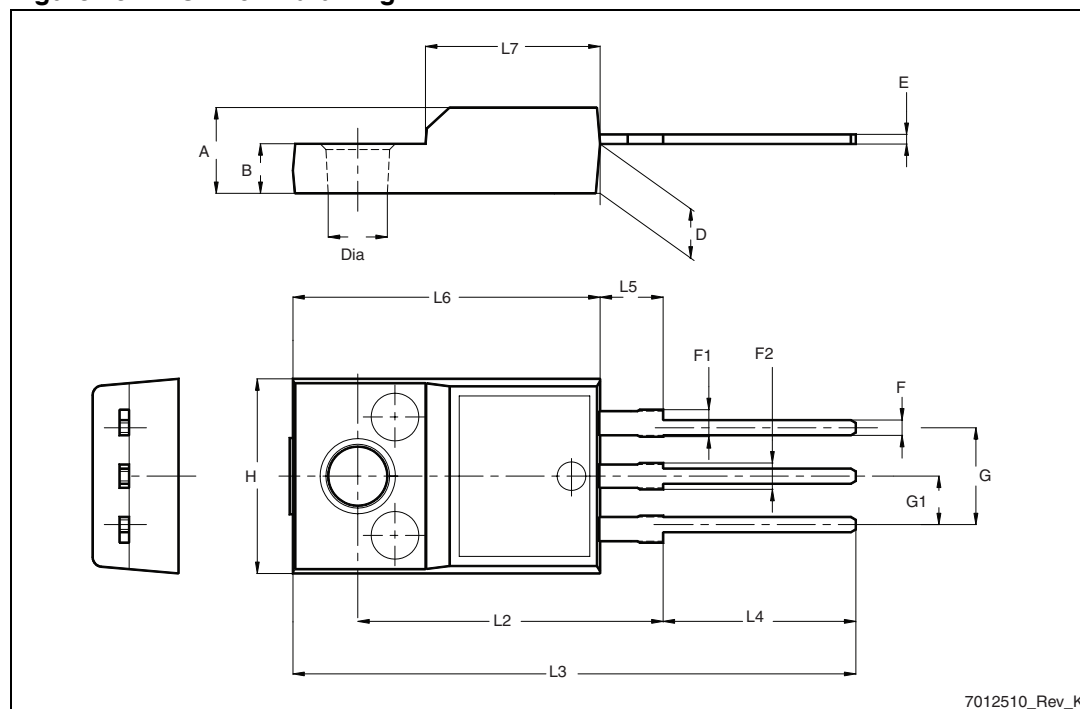
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 10. TO-220FP mechanical data

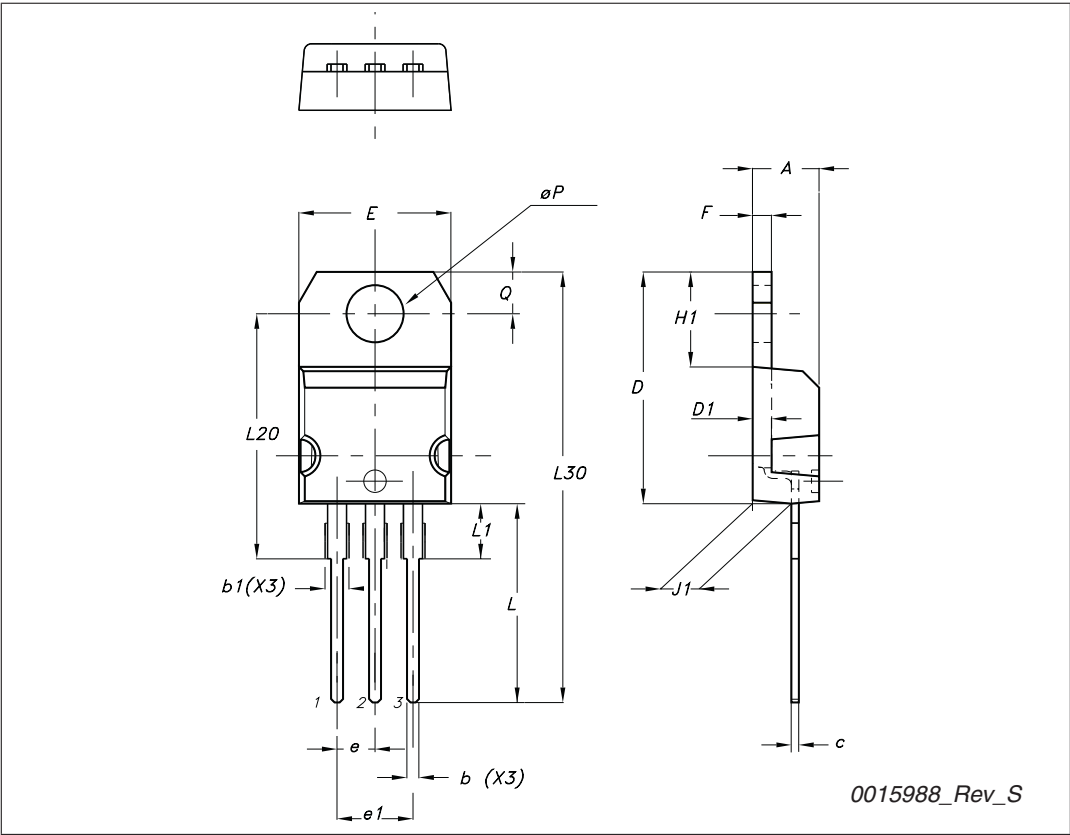
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 25. TO-220FP drawing



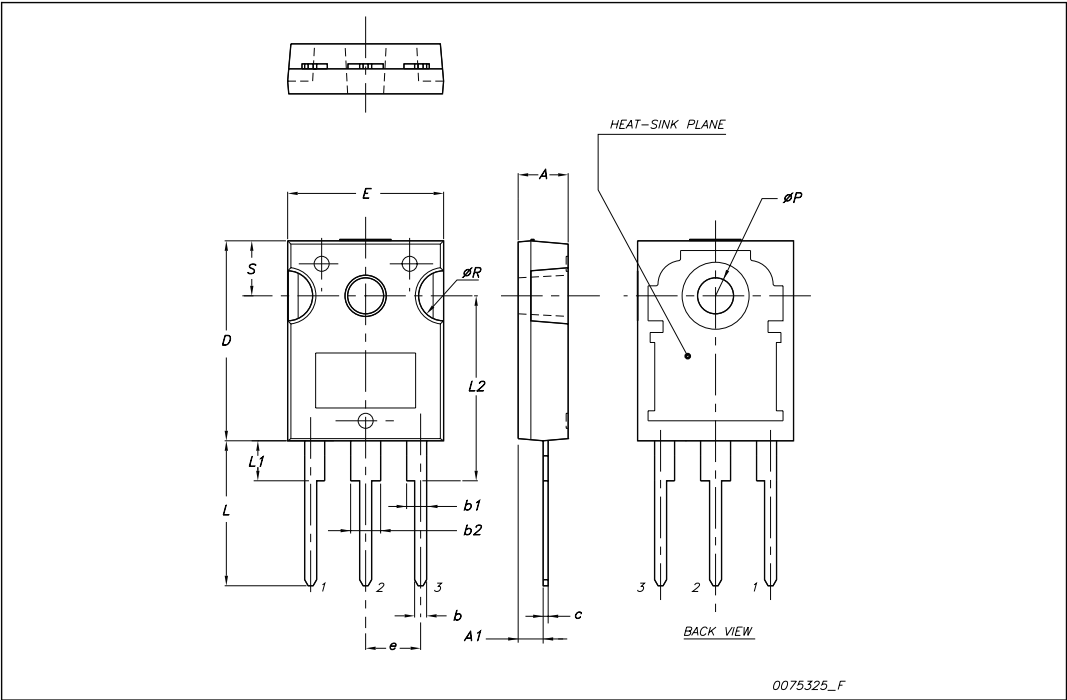
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95



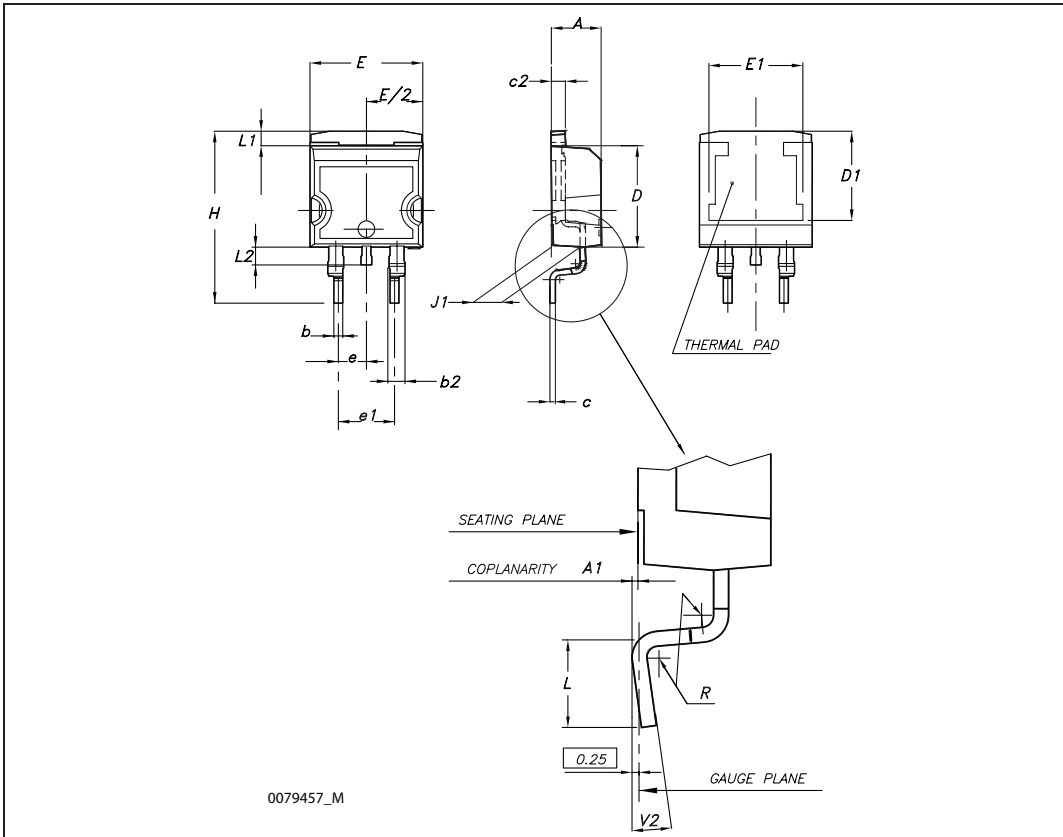
TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



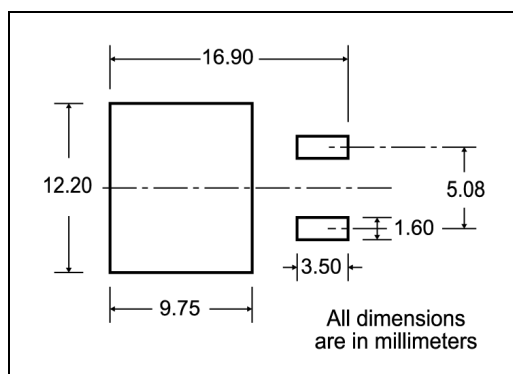
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

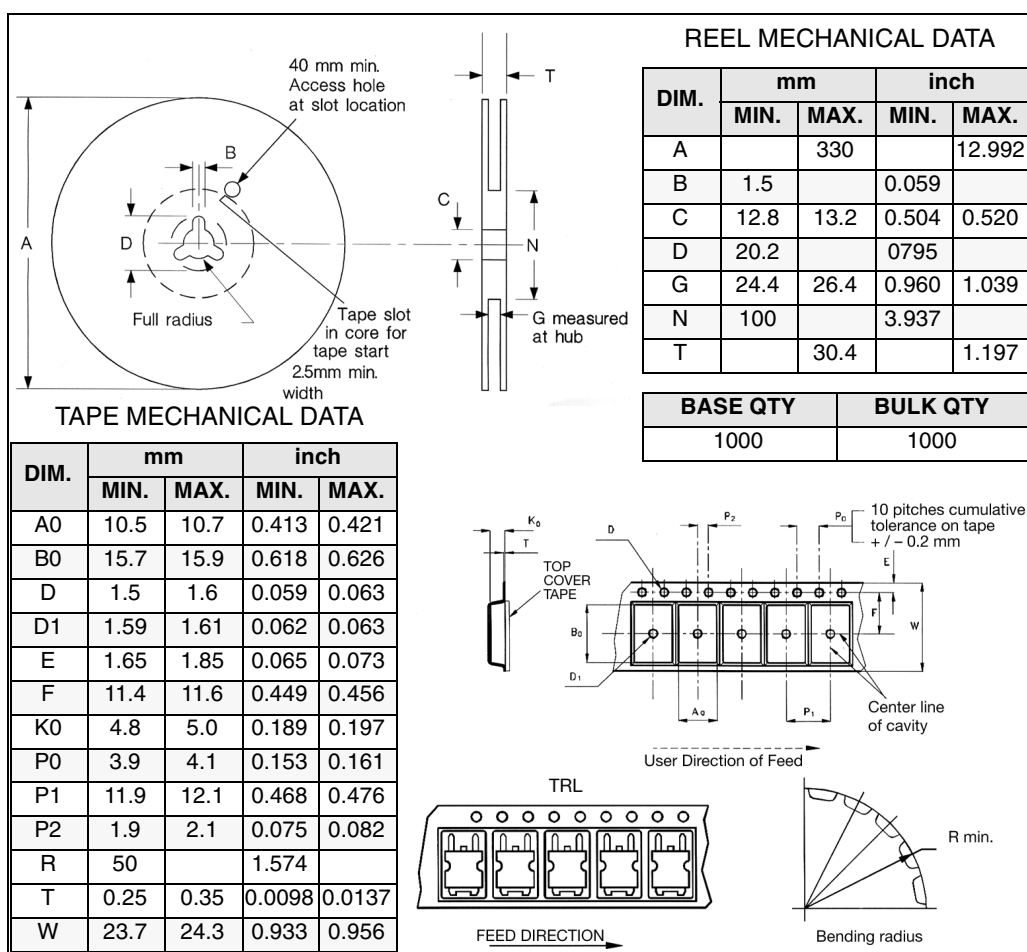


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 11. Revision history

Date	Revision	Changes
08-Sep-2005	2	Complete version
27-Oct-2005	3	Inserted ecopack indication
20-Jul-2006	4	New template, no content change
20-Mar-2007	5	Typo mistake on cover page
13-Jul-2007	6	Corrected unit on Table 5.: On/off states
19-May-2010	7	Corrected Figure 18: Maximum avalanche energy vs temperature

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